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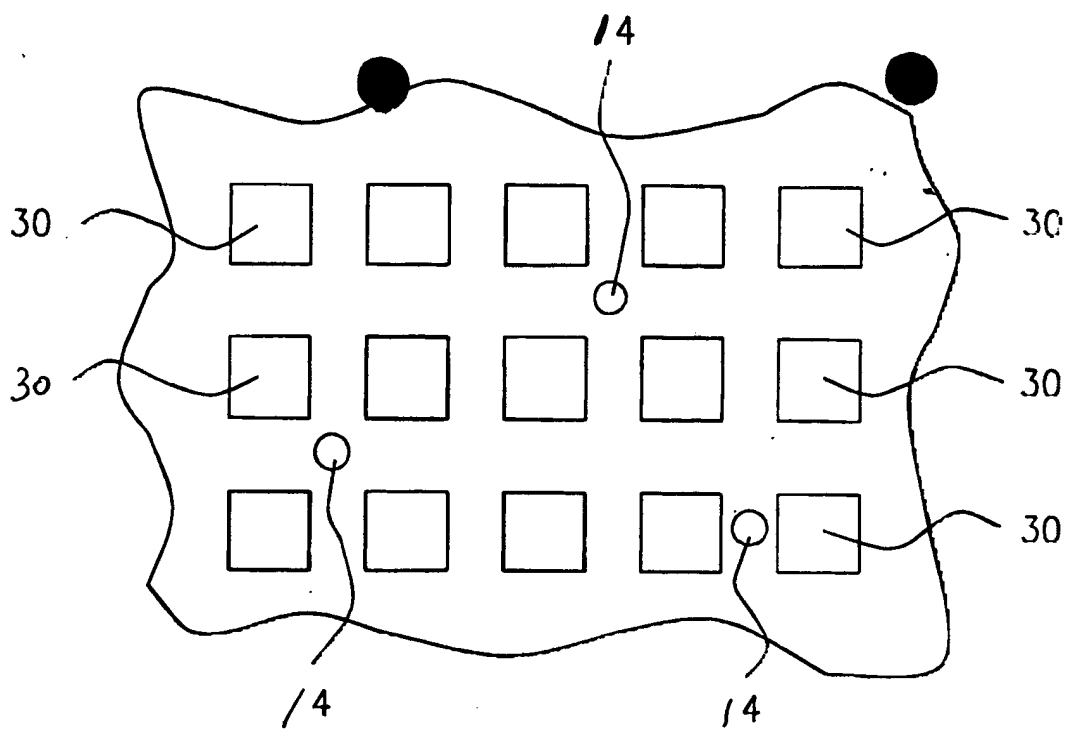


FIG 3

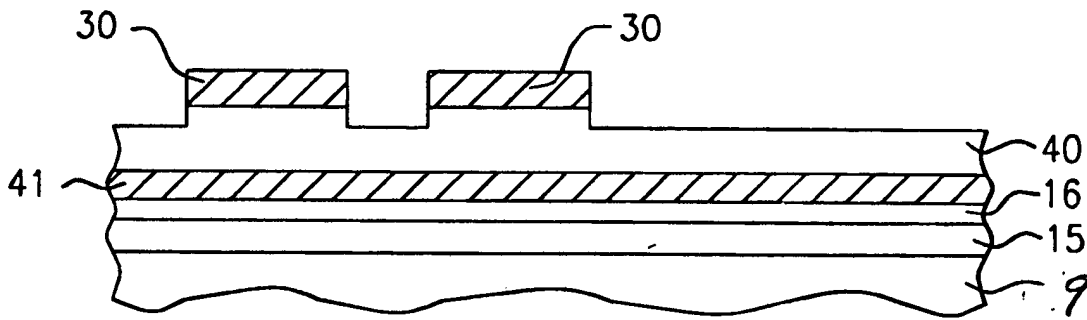


FIG 4

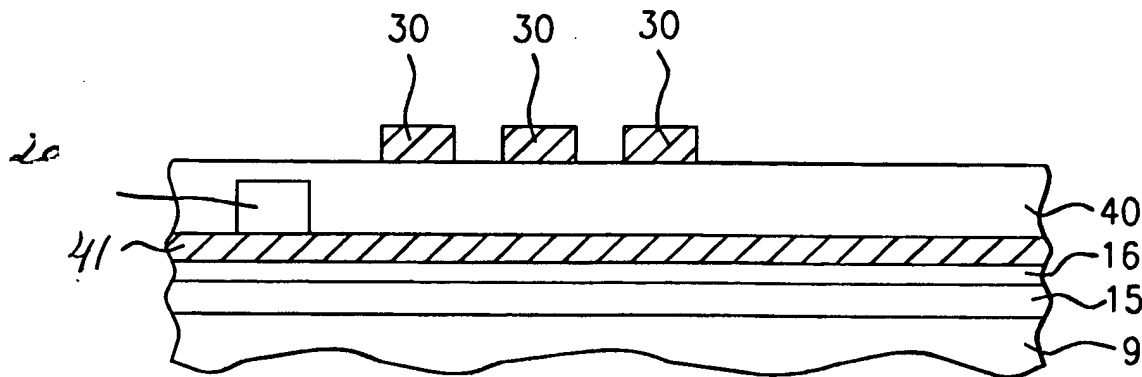


FIG 5

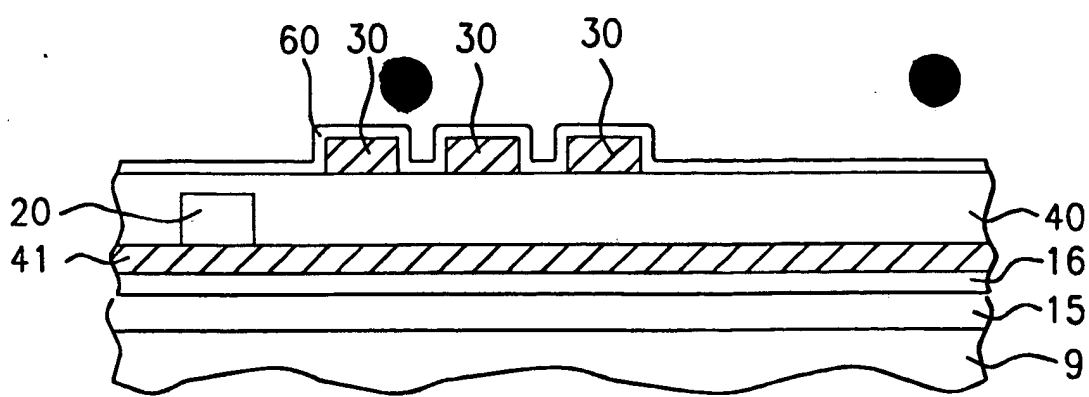


FIG 6

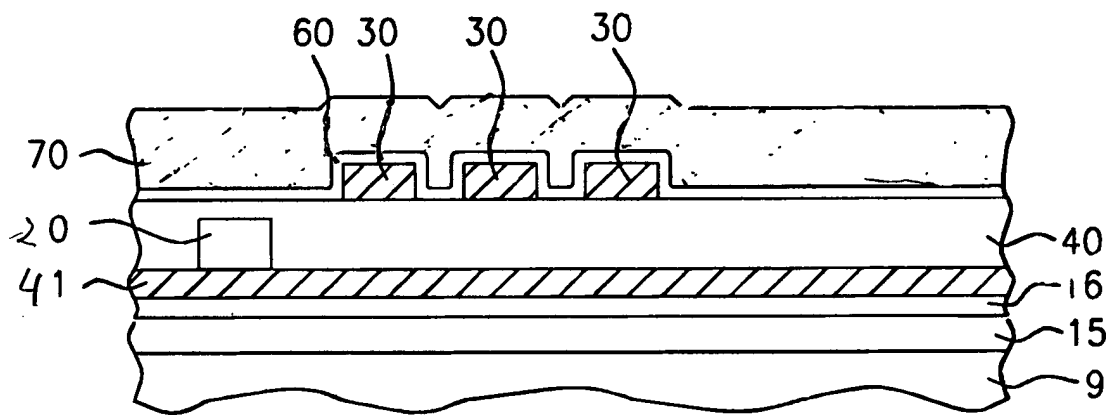


FIG 7

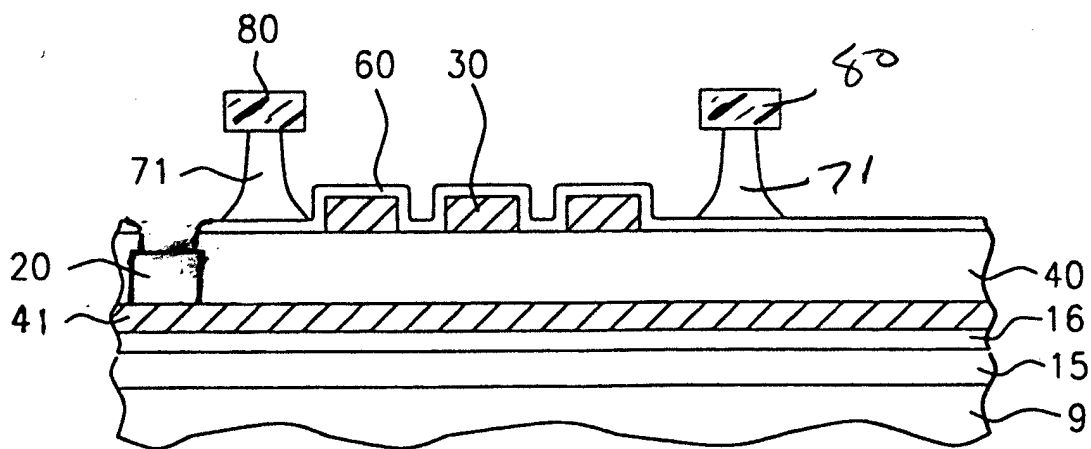


FIG 8

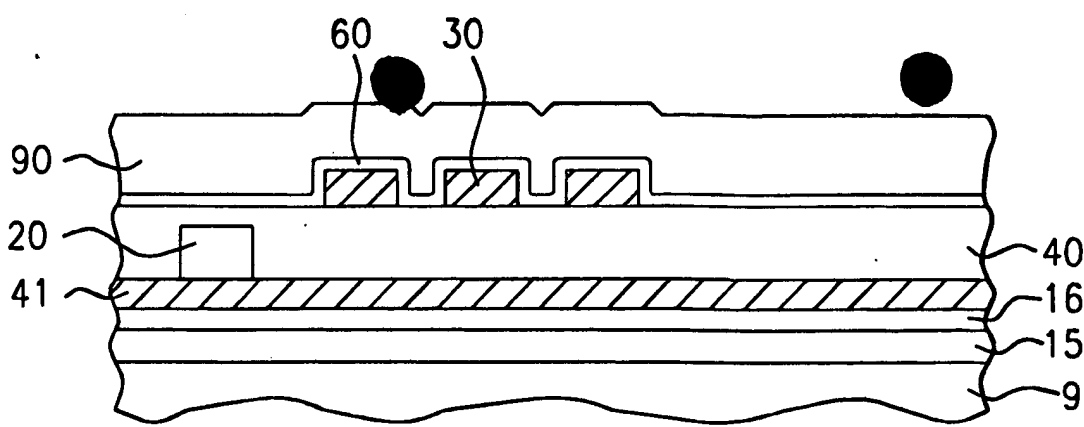


FIG 9

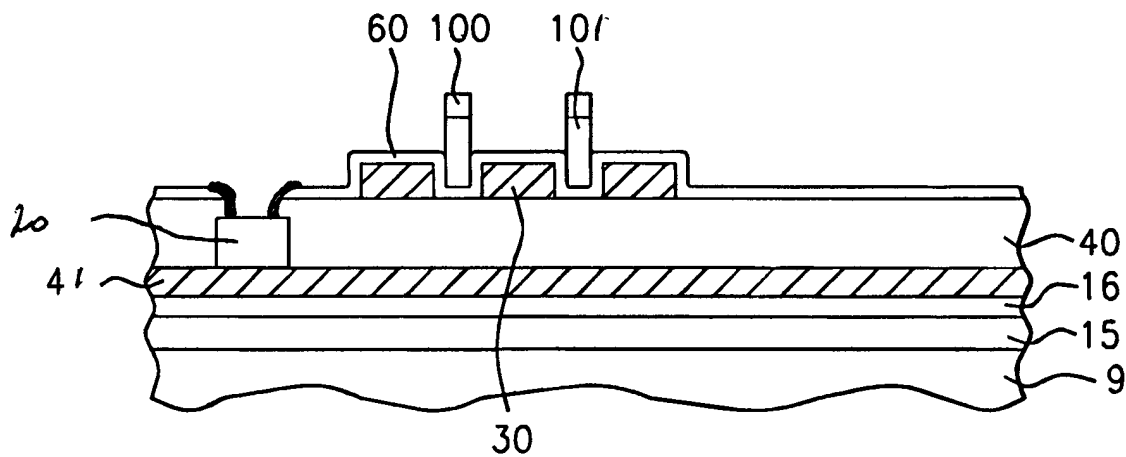


FIG 10

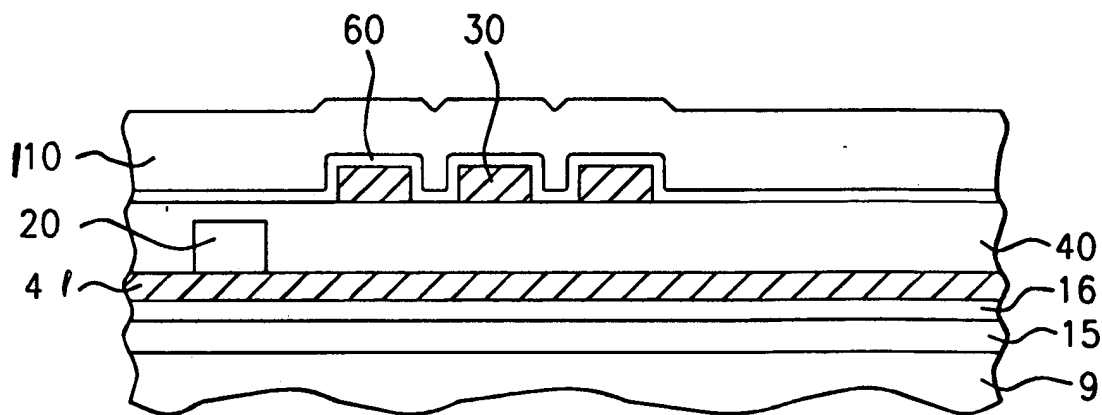


FIG 11



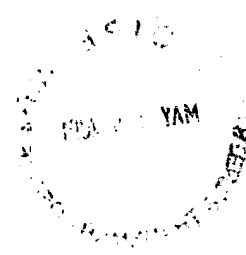


Fig. 1 is a cross-sectional view of a semiconductor device. The device includes a substrate with layers 9, 15, 16, and 40. A gate stack 20 is on the left, and a series of gates 30 and 60 are on the right. A contact 41 is on the left. A vertical structure 122 is between gates 30 and 60.

[illegible]

IG 14

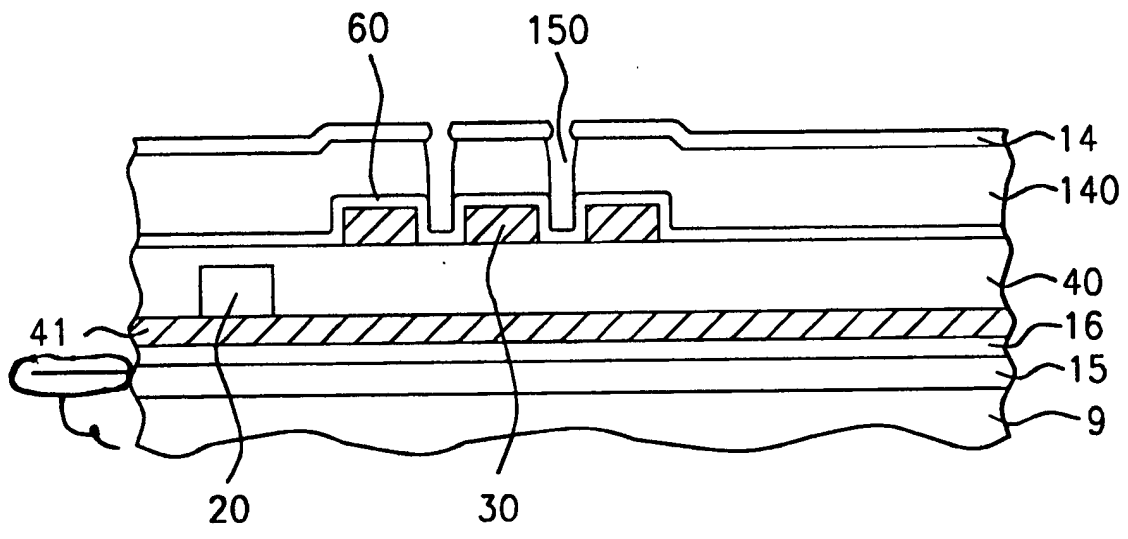


FIG 15

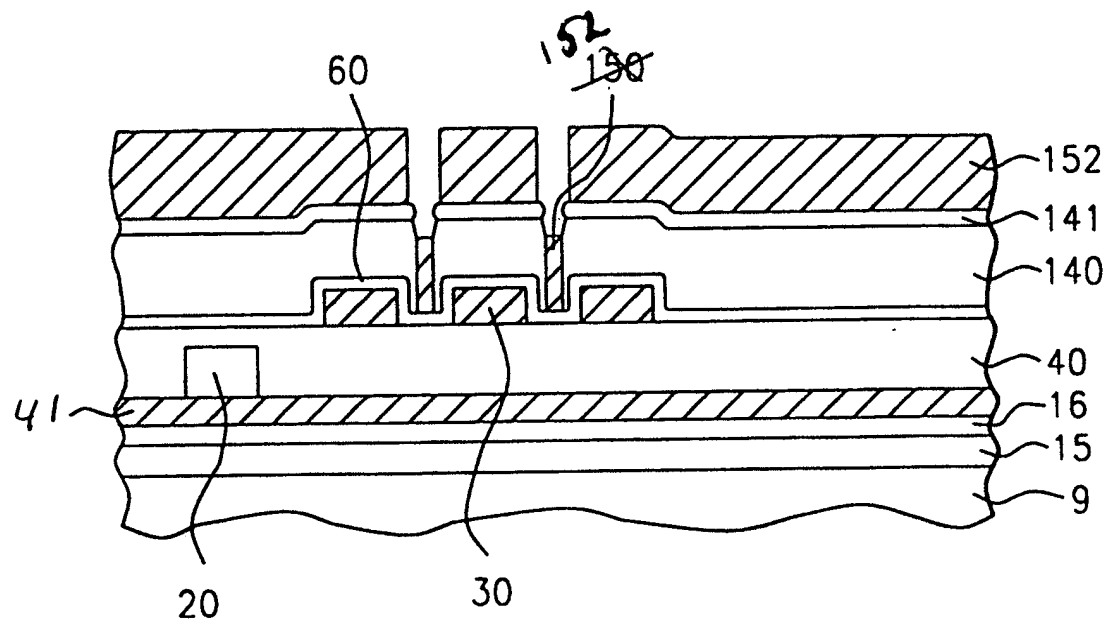
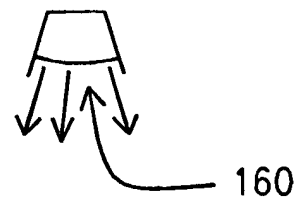


FIG 16